



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



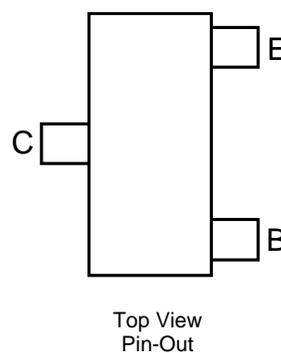
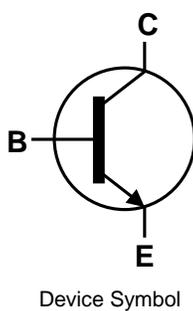
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Features

- $BV_{CEO} > 60V$
- $I_C = 1A$ Continuous Collector Current
- $I_{CM} = 2A$ Peak Pulse Current
- 500mW Power Dissipation
- Complementary PNP Type: NK-FMMT551

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (e3)
- Weight 0.008 grams (approximate)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	1	A
Peak Pulse Current	I _{CM}	2	A
Base Current	I _B	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

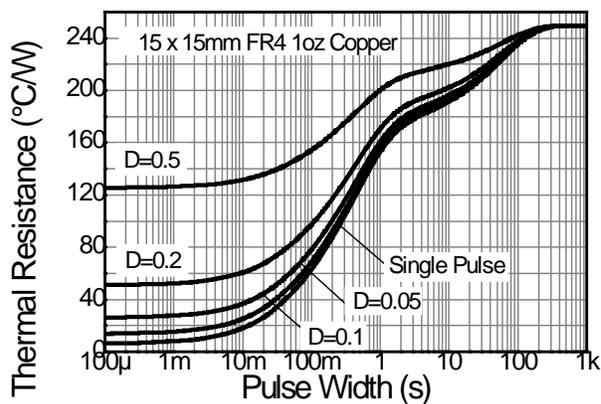
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	500	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	250	°C/W
Thermal Resistance, Junction to Lead (Note 6)	R _{θJL}	197	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

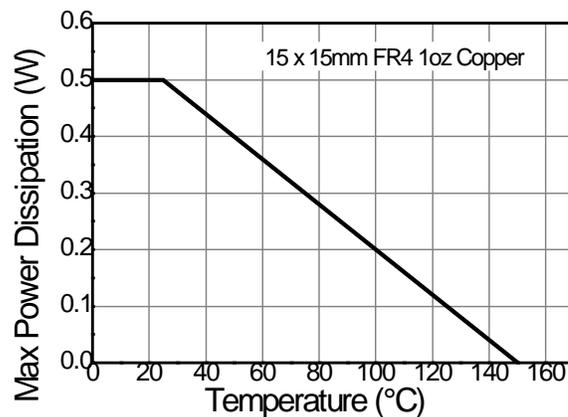
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Thermal resistance from junction to solder-point (at the end of the collector lead).
 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

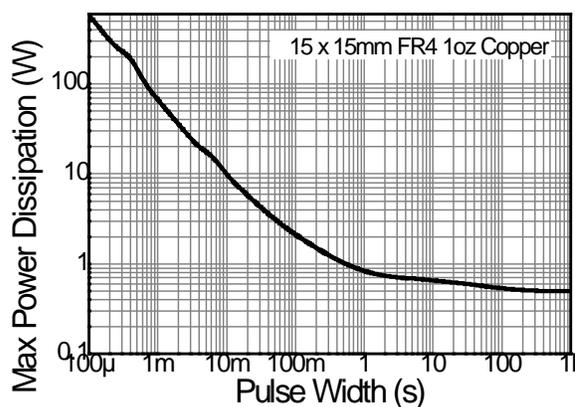
Thermal Characteristics and Derating Information



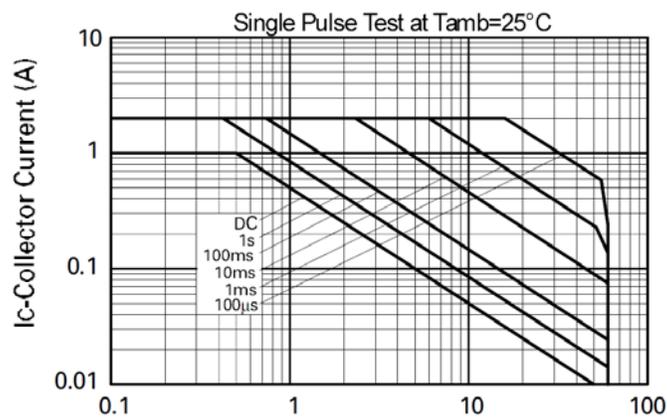
Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation



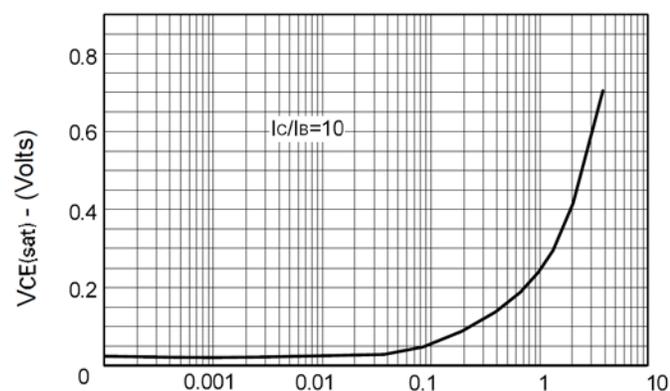
Safe Operating Area

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	60	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	—	—	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 60V
Emitter Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 4V
Static Forward Current Transfer Ratio (Note 8)	h _{FE}	50 10	— —	150 —	—	I _C = 150mA, V _{CE} = 10V I _C = 1A, V _{CE} = 10V
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	—	—	0.35	V	I _C = 150mA, I _B = 15mA
Base-Emitter Saturation Voltage(Note 8)	V _{BE(sat)}	—	—	1.1	V	I _C = 150mA, I _B = 15mA
Output Capacitance	C _{obo}	—	—	15	pF	V _{CB} = 10V. f = 1MHz
Transition Frequency	f _T	150	—	—	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz

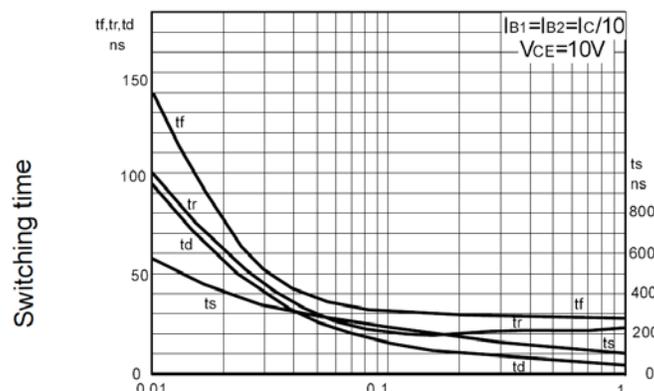
Note: 8. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



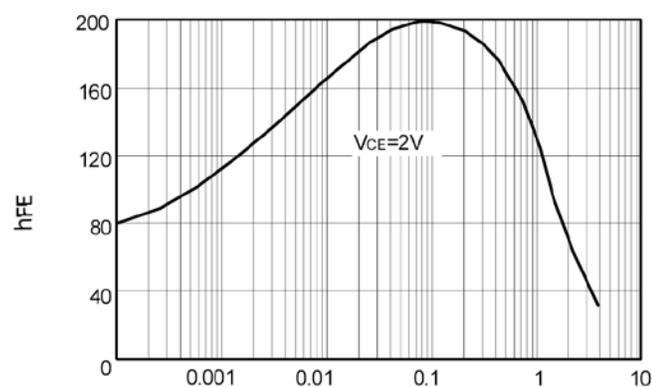
IC - Collector Current (Amps)

VCE(sat) v IC



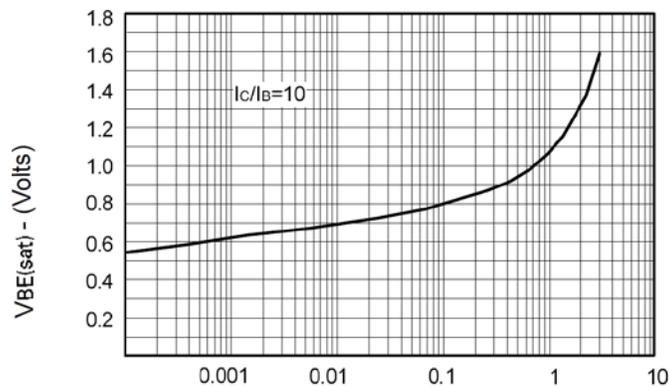
IC - Collector Current (Amps)

Switching Speeds



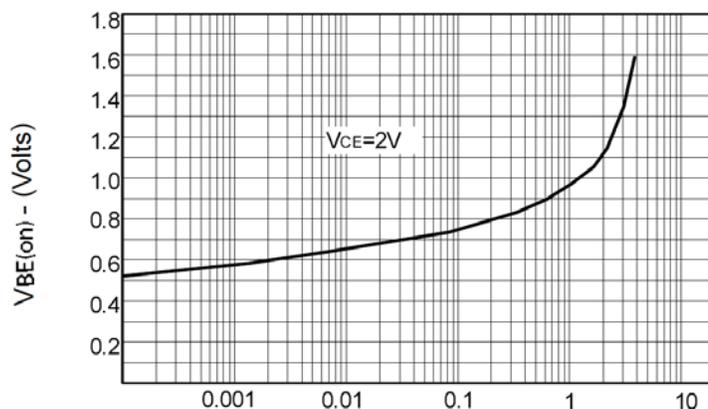
IC - Collector Current (Amps)

hFE v IC



IC - Collector Current (Amps)

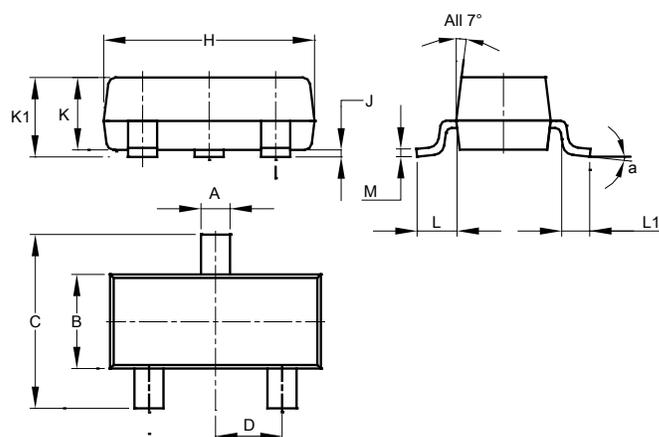
VBE(sat) v IC



IC - Collector Current (Amps)

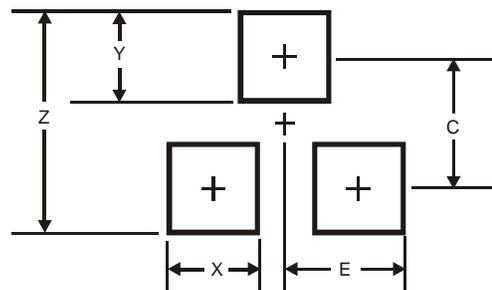
VBE(on) v IC

Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35